

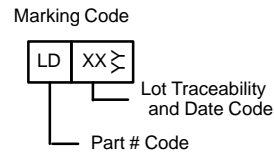
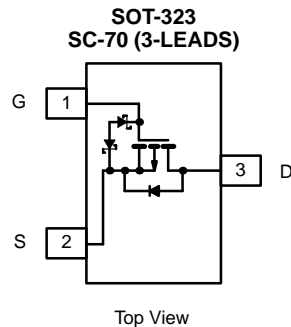


P-Channel 2.5-V (G-S) MOSFET

| PRODUCT SUMMARY | | |
|-----------------|---------------------------|------------|
| V_{DS} (V) | $r_{DS(on)}$ (Ω) | I_D (A) |
| -20 | 0.430 @ $V_{GS} = -4.5$ V | ± 0.72 |
| | 0.480 @ $V_{GS} = -3.6$ V | ± 0.68 |
| | 0.700 @ $V_{GS} = -2.5$ V | ± 0.56 |



ESD Protected
3000 V



| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED) | | | | | |
|---|----------------|--------------------------|--------------|------------------|---|
| Parameter | Symbol | 5 secs | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | -20 | | V | |
| Gate-Source Voltage | V_{GS} | ± 12 | | | |
| Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a | I_D | $T_A = 25^\circ\text{C}$ | ± 0.72 | ± 0.67 | A |
| | | $T_A = 70^\circ\text{C}$ | ± 0.58 | ± 0.54 | |
| Pulsed Drain Current | I_{DM} | ± 2.5 | | | |
| Continuous Diode Current (Diode Conduction) ^a | I_S | -0.28 | -0.24 | | |
| Maximum Power Dissipation ^a | P_D | $T_A = 25^\circ\text{C}$ | 0.34 | 0.29 | W |
| | | $T_A = 70^\circ\text{C}$ | 0.22 | 0.19 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to 150 | | $^\circ\text{C}$ | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|------------|----------------|---------|------|--------------------|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^a | R_{thJA} | $t \leq 5$ sec | 315 | 375 | $^\circ\text{C/W}$ |
| | | Steady State | 360 | 430 | |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 285 | 340 | | |

Notes

a. Surface Mounted on 1" x 1" FR4 Board.



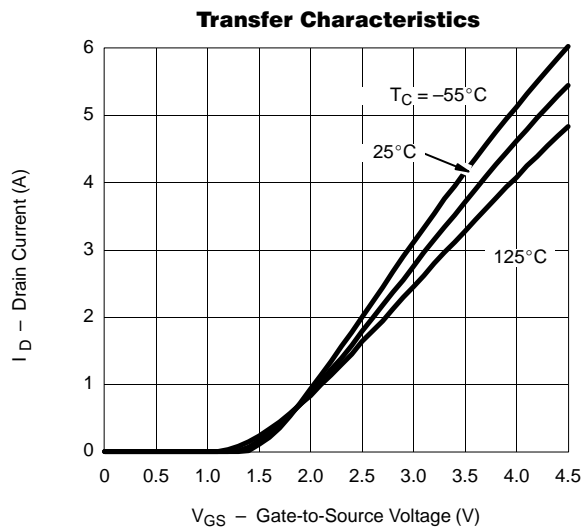
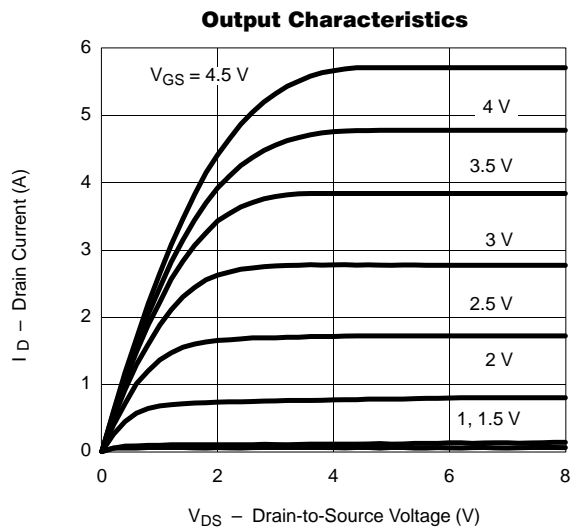
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|---------------------|--|------|-------|-------|------|
| Static | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = -250 μA | -0.6 | | | V |
| Gate-Body Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±4.5 V | | | ±1 | μA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = -20 V, V _{GS} = 0 V | | | -1 | μA |
| | | V _{DS} = -20 V, V _{GS} = 0 V, T _J = 70 °C | | | -5 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} = -5 V, V _{GS} = -4.5 V | -2.5 | | | A |
| Drain-Source On-State Resistance ^a | r _{DS(on)} | V _{GS} = -4.5 V, I _D = -1 A | | 0.360 | 0.430 | Ω |
| | | V _{GS} = -3.6 V, I _D = -0.7 A | | 0.400 | 0.480 | |
| | | V _{GS} = -2.5 V, I _D = -0.3 A | | 0.560 | 0.700 | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = -10 V, I _D = -1 A | | 1.7 | | S |
| Diode Forward Voltage ^a | V _{SD} | I _S = -1 A, V _{GS} = 0 V | | | -1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q _g | V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -1 A | | 1.9 | 2.5 | nC |
| Gate-Source Charge | Q _{gs} | | | 0.45 | | |
| Gate-Drain Charge | Q _{gd} | | | 0.44 | | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω | | 180 | 300 | ns |
| Rise Time | t _r | | | 410 | 655 | |
| Turn-Off Delay Time | t _{d(off)} | | | 560 | 900 | |
| Fall Time | t _f | | | 530 | 850 | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = -1 A, di/dt = 100 A/μs | | 435 | 700 | |

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

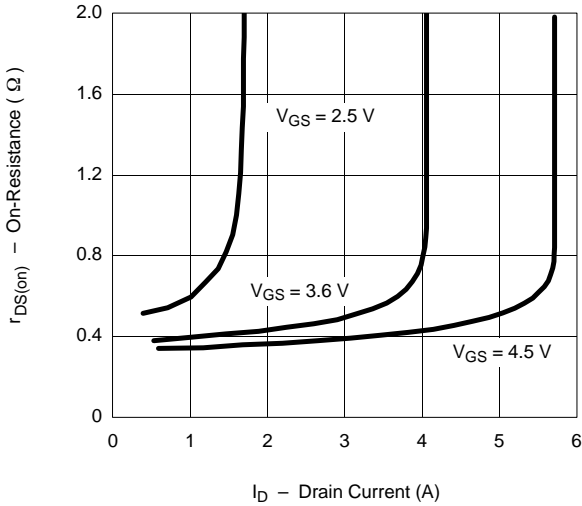
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



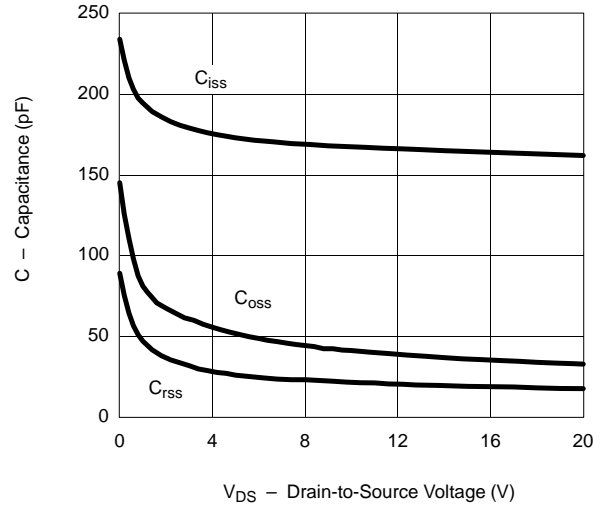


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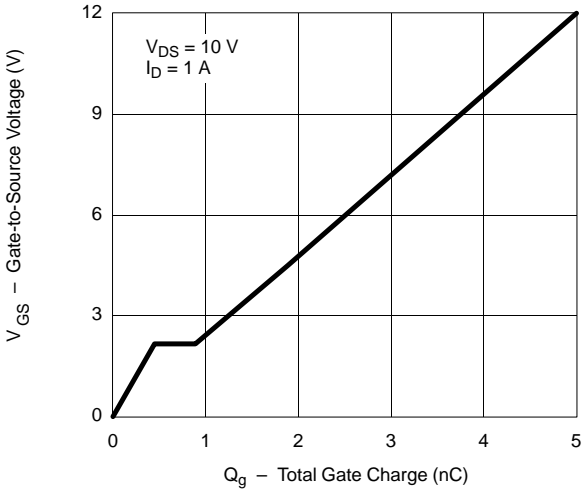
On-Resistance vs. Drain Current



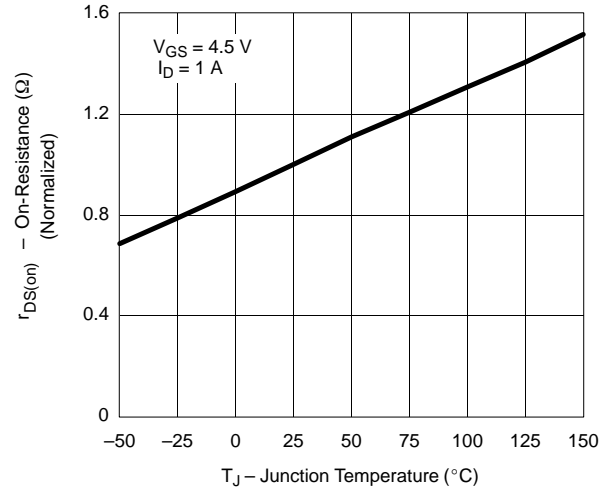
Capacitance



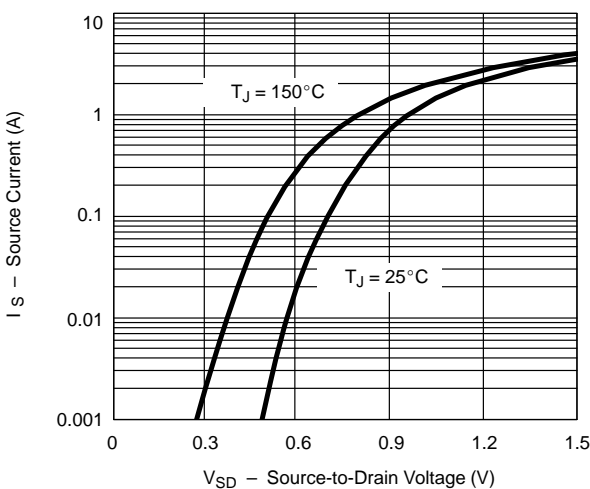
Gate Charge



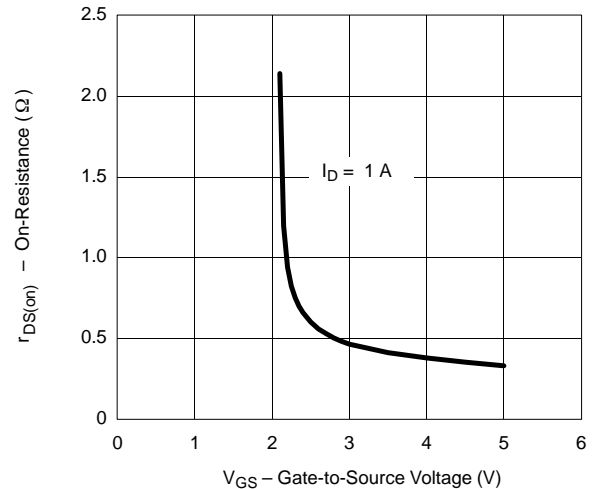
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



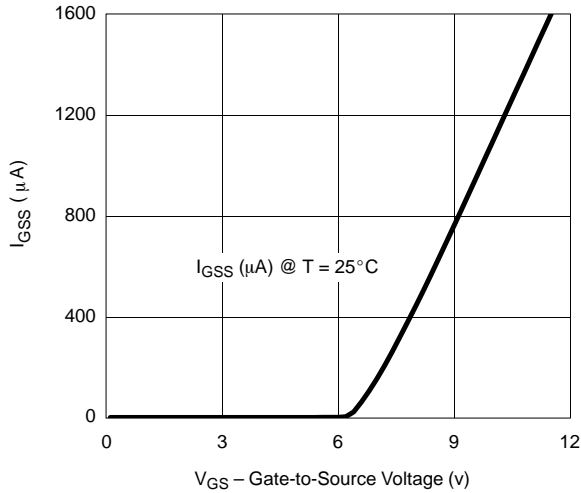
On-Resistance vs. Gate-to-Source Voltage



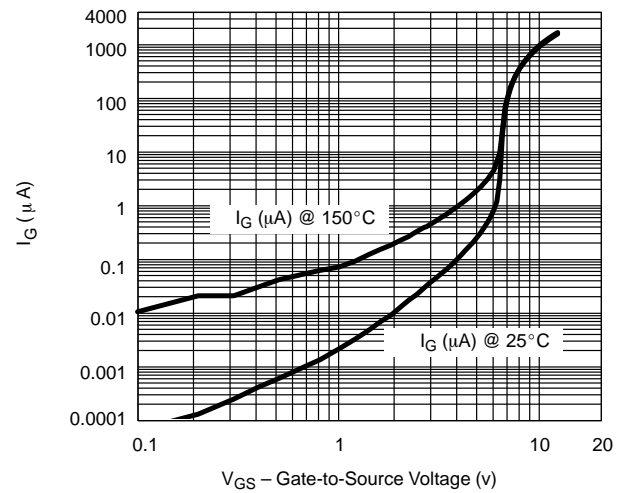


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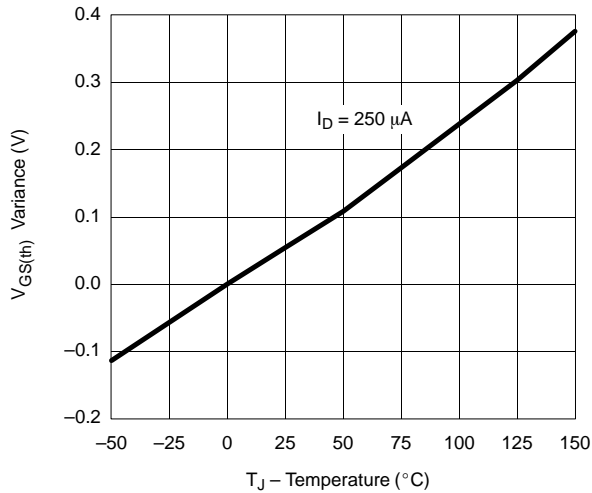
Gate-Current vs. Gate-Source Voltage



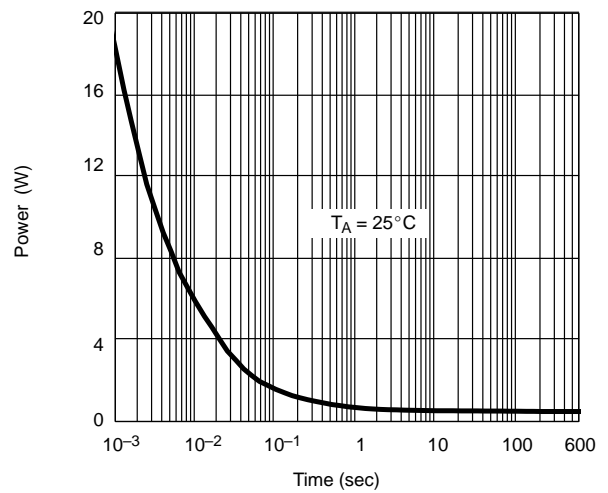
Gate-Source Voltage vs. Gate-Current



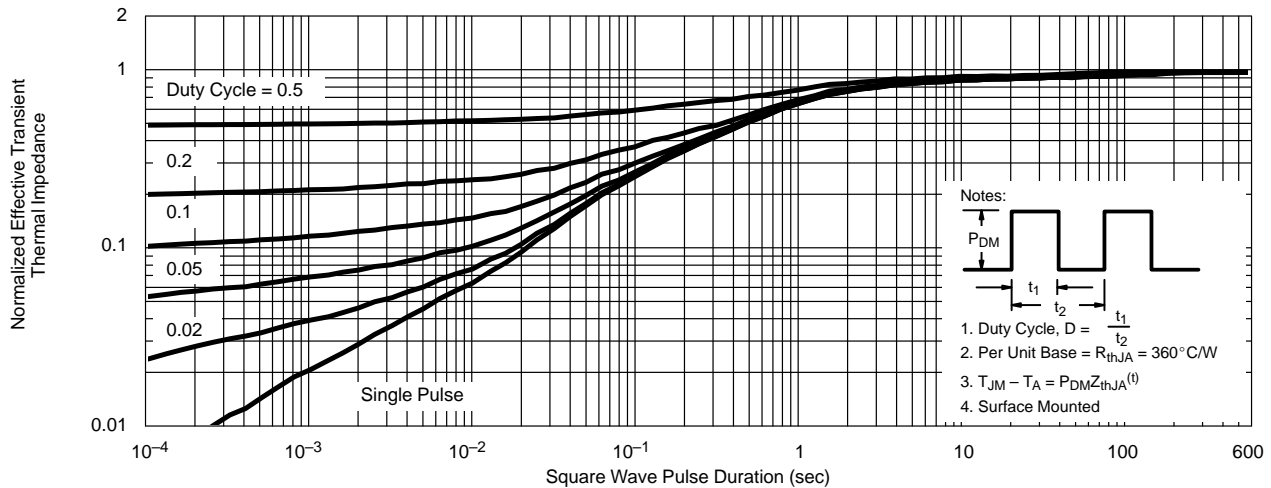
Threshold Voltage



Single Pulse Power

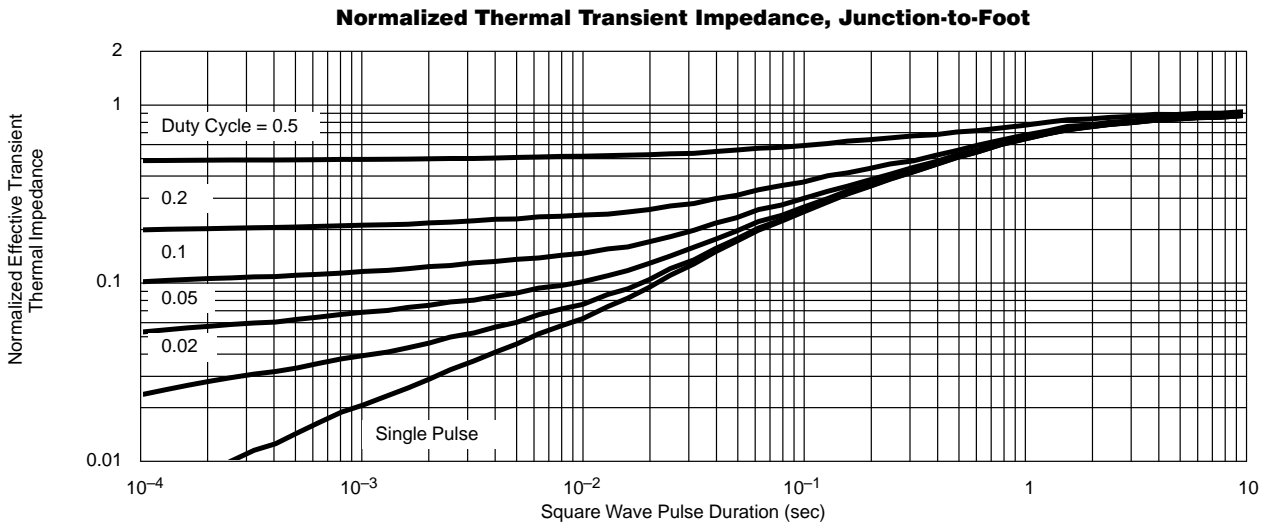


Normalized Thermal Transient Impedance, Junction-to-Ambient





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





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